

MA3Z080D, MA3Z080E

Silicon epitaxial planar type

For band switching

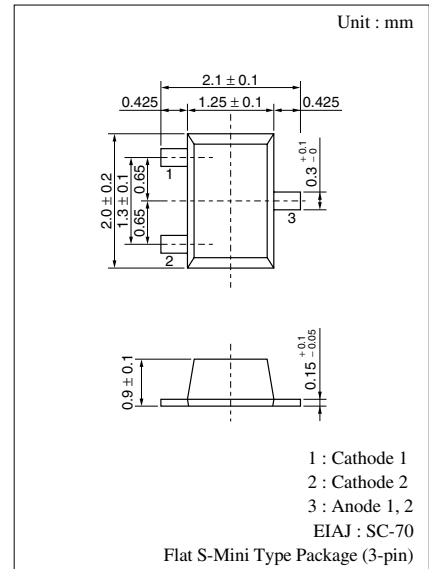
■ Features

- Low forward dynamic resistance r_f
- Less voltage dependence of diode capacitance C_D
- S-mini type package containing two elements, allowing downsizing of equipment and automatic insertion through the taping package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature*	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

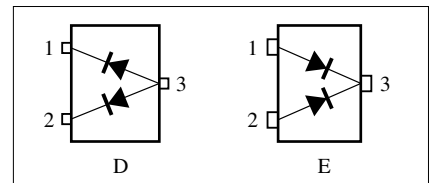
Note) * : Maximum ambient temperature during operation



Marking Symbol

- MA3Z080D : M1X
- MA3Z080E : M1Y

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 33\text{ V}$		0.01	100	nA
Forward voltage (DC)	V_F	$I_F = 100\text{ mA}$		0.92	1.0	V
Diode capacitance	C_D	$V_R = 6\text{ V}, f = 1\text{ MHz}$		0.9	1.2	pF
Forward dynamic resistance*	r_f	$I_F = 2\text{ mA}, f = 100\text{ MHz}$		0.65	0.85	Ω

Note) 1. Each characteristic is a standard for individual diodes

2. Rated input/output frequency: 100 MHz

3. * : r_f measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

